ABSTRACT

A ring-shaped reinforcing ring (13) formed of, for example, silicon, is adhered to one surface of a thinly processed semiconductor substrate (11). The reinforcing ring (13) is adhered thereto with an organic adhering material layer (14) formed of a metal or alloy with a relatively low melting point or polyimide resin with a relatively low melting point or softening point. Forming a metallic film (15) is executed in a state that the reinforcing ring (13) is adhered to the semiconductor substrate (11). The reinforcing ring (13) has the same outer diameter as that of the semiconductor substrate (11). Moreover, since a total thickness of the thinly processed semiconductor substrate (11) and the reinforcing ring (13) is substantially equal to that of the semiconductor substrate (11) which is not thinly processed, the semiconductor substrate (11) to which the reinforcing ring (13) is adhered can be transferred by the existing transferring unit.